

ABSTRACT OF THE DISCLOSURE

A semiconductor pressure sensor is presented. The pressure sensor includes a silicon substrate with a diaphragm that produces a distortion depending on the pressure. Strain gauges are provided on the main surface side of the silicon substrate with the diaphragm and are formed by conductive diffusion resistors different from the substrate. A getter is provided on the main surface side of the silicon substrate including the periphery of the strain gauges adjacent to the strain gauges. The getter includes the PN-junction area to which reverse bias is impressed so that the metal impurities of at least an Fe atom that are contained in the silicon substrate may be captured.